



CMLDM7120G

SURFACE MOUNT PICOMini™
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET

PICOMini™



SOT-563 CASE

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL	UNITS
Drain-Source Voltage	V_{DS}	V
Gate-Source Voltage	V_{GS}	V
Continuous Drain Current (Steady State)	I_D	A
Maximum Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	A
Power Dissipation (Note 1)	P_D	mW
Power Dissipation (Note 2)	P_D	mW
Power Dissipation (Note 3)	P_D	mW
Operating and Storage Junction Temperature	T_J, T_{Stg}	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}	$V_{GS}=8.0\text{V}, V_{DS}=0\text{V}$			10	μA
I_{GSSR}	$V_{GS}=8.0\text{V}, V_{DS}=0\text{V}$			10	μA
I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			10	μA
BV_{DSS}	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	20			V
$V_{GS(\text{th})}$	$V_{DS}=10\text{V}, I_D=1.0\text{mA}$	0.5		1.2	V
V_{SD}	$V_{GS}=0\text{V}, I_S=1.0\text{A}$			1.1	V
$r_{DS(\text{ON})}$	$V_{GS}=4.5\text{V}, I_D=0.5\text{A}$		0.075	0.10	Ω
$r_{DS(\text{ON})}$	$V_{GS}=2.5\text{V}, I_D=0.5\text{A}$		0.10	0.14	Ω
$r_{DS(\text{ON})}$	$V_{GS}=1.5\text{V}, I_D=0.1\text{A}$		0.20	0.25	Ω
g_{fs}	$V_{DS}=10\text{V}, I_D=0.5\text{A}$		2.5		s
C_{rss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		45		pF
C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		220		pF
C_{oss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		120		pF
t_{on}	$V_{DD}=10\text{V}, V_{GS}=5.0\text{V}, I_D=0.5\text{A}$		25		ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=5.0\text{V}, I_D=0.5\text{A}$		140		ns

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0 mm^2

(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0 mm^2

(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4 mm^2

Central™
Semiconductor Corp.

DESCRIPTION:

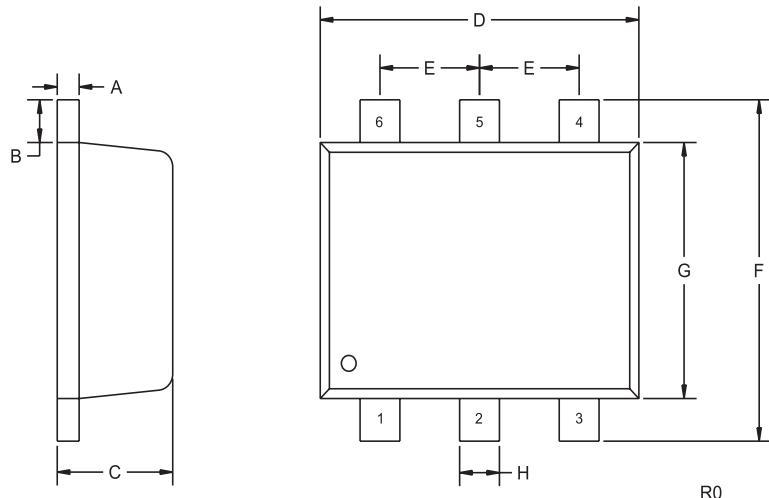
The CENTRAL SEMICONDUCTOR CMLDM7120G is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low $r_{DS(\text{ON})}$ and Low Threshold Voltage.

MARKING CODE: C7G

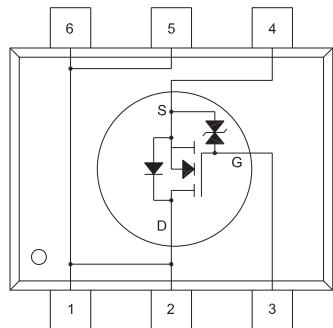
FEATURES:

- Device is **Halogen Free** by design
- Device is **RoHS** compliant
- ESD protection up to 2kV
- Low $r_{DS(\text{ON})}$ (0.25Ω MAX @ $V_{GS}=1.5\text{V}$)
- High current ($I_D=1.0\text{A}$)
- Logic level compatibility

SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:

- 1) DRAIN
- 2) DRAIN
- 3) GATE
- 4) SOURCE
- 5) DRAIN
- 6) DRAIN

MARKING CODE: C7G

R2 (12-June 2008)